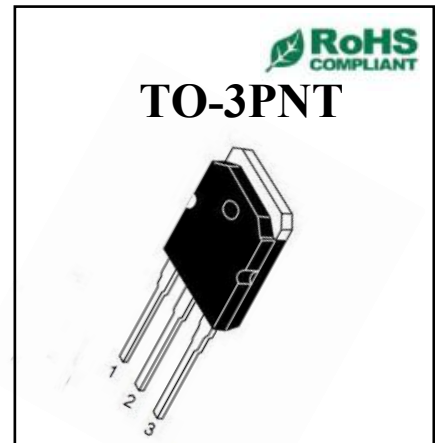


NPN/PNP Complementary Silicon Power Transistors

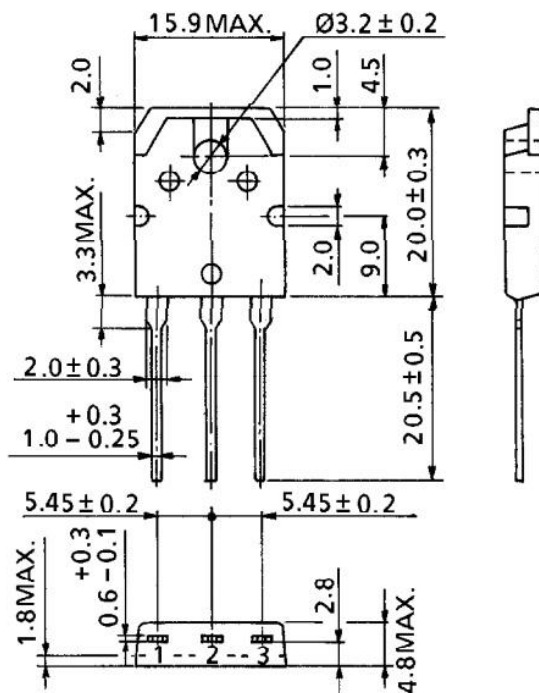
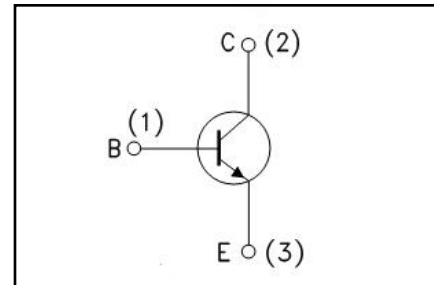
◆ Features:

- ◇ High efficiency, low deviation
高效率, 低偏差
- ◇ Small input impedance, low consumption of power
输入阻抗小, 功耗低
- ◇ Resistant of high temperature, high humidity
抗高温、高湿
- ◇ Good stability, reliability
稳定性好, 可靠性高



◆ Applications

- ◇ Audio amplifier
音频放大器
- ◇ Switching applications
开关应用
- ◇ Complement to Type OSB688(PNP)
与 OSB688 互补应用
- ◇ Recommend for 100W high fidelity audio frequency amplifier output stage applications
推荐用于 100W 高保真音频放大器输出级应用



◆ Absolute Maximum Ratings ($T_c=25^{\circ}\text{C}$)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	150	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	120	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	7	V
I _c	Collector Current-Continuous 集电极连续电流	10	A
I _B	Base Current-Continuous 基极连续电流	1	A
PC	Collector Power Dissipation 耗散功率	100	W
T _j	Max. Operating junction temperature 最大结温	150	°C
T _{stg}	Storage Temperature 存储温度	-65 ~ +150	°C

◆ Electrical characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I _{CBO}	Collector Cutoff Current 集电极截止电流	--	--	1.0	μA	V _{CB} =120V, I _E =0
I _{EBO}	Emitter Cutoff Current 发射极截止电流	--	--	10	μA	V _{EB} =10V, I _C =0
BV _{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	120	--	--	V	I _C =30mA, I _B =0
V _{CE(sat)}	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压	--	--	2.0	V	I _C =5A, I _B =0.5A
h _{FE}	DC Current Gain(Note 1) 直流电流增益	80	--	160		I _C =1A, V _{CE} =5V
f _T	Current-Gain—Bandwidth 电流增益带宽	10	--	--	MHz	V _{CE} =5V, I _C =1A, f=1MHz

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.